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11/09/2009

INTERNATIONAL BUSINESS MACHINES CORPORATION DEPT. 18G BLDG. 321-482 2070 ROUTE 52 HOPEWELL JUNCTION, NY 12533

EXAMINER				
HAMLIN, JR, KENNETH B				
ART UNIT	PAPER NUMBER			

2893

DATE MAILED: 11/09/2009

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/597,288	07/19/2006	Dureseti Chidambarrao	FIS920030347US1	8869

TITLE OF INVENTION: VERTICAL FIN-FET MOS DEVICES

APPLN. TYPE	SMALL ENTITY	ISSUE FEE DUE	PUBLICATION FEE DUE	PREV. PAID ISSUE FEE	TOTAL FEE(S) DUE	DATE DUE
nonprovisional	NO	\$1510	\$300	\$0	\$1810	02/09/2010

THE APPLICATION IDENTIFIED ABOVE HAS BEEN EXAMINED AND IS ALLOWED FOR ISSUANCE AS A PATENT. PROSECUTION ON THE MERITS IS CLOSED. THIS NOTICE OF ALLOWANCE IS NOT A GRANT OF PATENT RIGHTS. THIS APPLICATION IS SUBJECT TO WITHDRAWAL FROM ISSUE AT THE INITIATIVE OF THE OFFICE OR UPON PETITION BY THE APPLICANT. SEE 37 CFR 1.313 AND MPEP 1308.

THE ISSUE FEE AND PUBLICATION FEE (IF REQUIRED) MUST BE PAID WITHIN THREE MONTHS FROM THE MAILING DATE OF THIS NOTICE OR THIS APPLICATION SHALL BE REGARDED AS ABANDONED. THIS STATUTORY PERIOD CANNOT BE EXTENDED. SEE 35 U.S.C. 151. THE ISSUE FEE DUE INDICATED ABOVE DOES NOT REFLECT A CREDIT FOR ANY PREVIOUSLY PAID ISSUE FEE IN THIS APPLICATION. IF AN ISSUE FEE HAS PREVIOUSLY BEEN PAID IN THIS APPLICATION (AS SHOWN ABOVE), THE RETURN OF PART B OF THIS FORM WILL BE CONSIDERED A REQUEST TO REAPPLY THE PREVIOUSLY PAID ISSUE FEE TOWARD THE ISSUE FEE NOW DUE.

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INTERNATIONAL BUSINESS MACHINES CORPORATION DEPT. 18G BLDG. 321-482 2070 ROUTE 52 HOPEWELL JUNCTION, NY 12533									
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									(Date)
APPLICATION NO.	FILING DATE		FIRST NAMED INVEN	NTOR		ATTO	RNEY DOCKET NO.	CON	FIRMATION NO.
10/597,288 TITLE OF INVENTION	07/19/2006 I: VERTICAL FIN-FET	MOS DEVICES	Dureseti Chidamba	rrao		F1S	S920030347US1		8869
APPLN. TYPE	SMALL ENTITY	ISSUE FEE DUE	PUBLICATION FEE I	DUE	PREV. PAID ISSUE	E FEE	TOTAL FEE(S) DUE	\top	DATE DUE
nonprovisional	NO	\$1510	\$300		\$0		\$1810		02/09/2010
EXAM	IINER	ART UNIT	CLASS-SUBCLAS	S					
HAMLIN, JR,	KENNETH B	2893	257-347000						
Address form PTO/Si "Fee Address" ind PTO/SB/47; Rev 03-0 Number is required. 3. ASSIGNEE NAME A	lication (or "Fee Address 22 or more recent) attack and RESIDENCE DATA less an assignee is ident the in 37 CFR 3.11. Comp	" Indication form	or agents OR, alte (2) the name of a registered attorney 2 registered paten listed, no name with THE PATENT (print)	singley or a strong traction at the strong traction or type the party and a strong traction at the strong traction	e firm (having as a gent) and the name reys or agents. If a printed. The printed represents of	memb es of up no nam	er a 2 o to e is 3 dentified below, the de		nt has been filed for
Please check the appropr	riate assignee category or	categories (will not be pr	rinted on the patent):		1ndividual 🖵 Co	rporati	on or other private gro	oup enti	ity Government
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5. Change in Entity Sta a. Applicant claim	i tus (from status indicate is SMALL ENTITY stati	*	☐ b. Applicant is n	o long	ger claiming SMAL	L ENT	TITY status. See 37 CI	FR 1.27	7(g)(2).
NOTE: The Issue Fee an	d Publication Fee (if req	uired) will not be accepte ites Patent and Trademark	d from anyone other t	`					
Authorized Signature					Date				
This collection of inform an application. Confiden submitting the complete this form and/or suggest Box 1450, Alexandria, V Alexandria, Virginia 223	/10g1n1a_2231.5-145U17U	CFR 1.311. The information U.S.C. 122 and 37 CFR to USPTO. Time will vary rden, should be sent to the NOT SEND FEES OR	on is required to obtai 1.14. This collection depending upon the e Chief Information (COMPLETED FORM	n or reis est indiv Office AS TO	etain a benefit by thimated to take 12 nidual case. Any corr, U.S. Patent and 'DTHIS ADDRESS	ne publ ninutes mment Traden . SENI	ic which is to file (and to complete, including son the amount of times of the complete of the complete of the commissioner of the complete of the commissioner of the complete of the complet	l by the g gathe ne you artment for Pate	e USPTO to process) ering, preparing, and require to complete of Commerce, P.O. ents, P.O. Box 1450,

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APPLICATION NO. FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO. CONFIRMATION NO. 10/597,288 07/19/2006 FIS920030347US1 8869 Dureseti Chidambarrao **EXAMINER** 32074 7590 11/09/2009 HAMLIN, JR, KENNETH B INTERNATIONAL BUSINESS MACHINES CORPORATION DEPT, 18G ART UNIT PAPER NUMBER BLDG. 321-482 2893 2070 ROUTE 52 DATE MAILED: 11/09/2009 HOPEWELL JUNCTION, NY 12533

Determination of Patent Term Extension under 35 U.S.C. 154 (b)

(application filed after June 7, 1995 but prior to May 29, 2000)

The Patent Term Extension is 0 day(s). Any patent to issue from the above-identified application will include an indication of the 0 day extension on the front page.

If a Continued Prosecution Application (CPA) was filed in the above-identified application, the filing date that determines Patent Term Extension is the filing date of the most recent CPA.

Applicant will be able to obtain more detailed information by accessing the Patent Application Information Retrieval (PAIR) WEB site (http://pair.uspto.gov).

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (571)-272-7702. Questions relating to issue and publication fee payments should be directed to the Customer Service Center of the Office of Patent Publication at 1-(888)-786-0101 or (571)-272-4200.

	Application No.	Applicant(s)		
	10/597,288	CHIDAMBARRAO ET AL.		
Notice of Allowability	Examiner	Art Unit		
	KENNETH HAMLIN	2893		
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this apport or other appropriate communication IGHTS. This application is subject to	olication. If not included will be mailed in due course. THIS		
1. This communication is responsive to				
2. ☑ The allowed claim(s) is/are <u>1-21</u> .				
 Acknowledgment is made of a claim for foreign priority unally all bloomests complete all long and long all bloomests and long all long all long and long all long all long and long all long all long all long and long all long	e been received. e been received in Application No			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	IENT of this application.			
 A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give 				
5. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.			
(a) ☐ including changes required by the Notice of Draftspers	on's Patent Drawing Review (PTO-	948) attached		
1) hereto or 2) to Paper No./Mail Date	•			
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment or in the C	Office action of		
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t				
6. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT				
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date 20080428, 20060719 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	5. Notice of Informal P 6. Interview Summary Paper No./Mail Dat 7. Examiner's Amendr 8. Examiner's Stateme 9. Other	(PTO-413), ee		

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Dan Schnurman on 11/02/2009.

The application has been amended as follows:

Claim 2 has been canceled.

Replace Claim 1 with the following:

A vertical Fin-FET semiconductor device characterized by:

At least one vertical semiconductor fin (12A) disposed on an insulator layer (4);

Doped source (26A) and drain regions (28A) in bottom and top portions of the at least one semiconductor fin (12A); and

Gate conductors (24A, 24B) disposed along vertical sidewalls of the at least one semiconductor fin (12A) and separated therefrom by thin gate insulators (22).

Source conductors (18A, 18B) contacting the source region (26A) on opposite sides of the at least one semiconductor fin (12A);

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At least one source contract (38A) connecting to at least one source conductor (18A, 18B);

At least one drain contact (40A) connecting to the drain region (28A) of the at least one semiconductor fin (12A);

A vertical channel region in the fin (12A) between the source region (26A) and the drain region (28A); and

At least one gate contact (42A) connection to at least one gate conductor (24A, 24B).

Line 1, Claim 3 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 4 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 5 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 6 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 7 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 8 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 9 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 10 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 12 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 13 replace, "according to claim 2" with - according to claim 1 -.

Line 1, Claim 14 replace, "according to claim 2" with - according to claim 1 -.

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Drawings

The drawings filed on 7/19/2006 and 4/20/2009 have been accepted.

Allowable Subject Matter

Claims 1-21 have been deemed as Allowable Subject Matter

The following is an examiner's statement of reasons for allowance:

Regarding Claims 1 and 15; the cited prior art of record does not teach or fairly suggest a vertical Fin-FET semiconductor device comprising, along with the other claimed features, source conductors contacting the source region on opposite sides of the at least one vertical fin; at least one source contact connecting to at least one source conductor; at least one drain contact connecting to the drain region of the at least one semiconductor fin; and at least one gate contact connecting to at least one gate conductor.

Regarding Claim 20; the cited prior art of record does not teach or fairly suggest a method of forming a vertical Fin-FET device comprising, along with the other claimed features, the step of forming metal source, drain and gate contacts by Damascene processes of selective etching, metal fill, and chem-mech polishing.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Relevant Cited Prior Art

Fitch et al. (US 5,414,289) discloses a vertical Fin-FET semiconductor device characterized by at least one vertical semiconductor fin disposed on an insulator layer Doped source and drain regions in bottom and top portions of the at least one semiconductor fin; and gate conductors disposed along vertical sidewalls of the at least one semiconductor fin and separated therefrom by thin gate insulators; and a vertical channel region in the fin between the source region and the drain region.

Fitch et al. fails to disclose source conductors contacting the source region on opposite sides of the at least one semiconductor fin; At least one source contact connecting to at least one source conductor; at least one drain contact connecting to the drain region of the at least one semiconductor fin; at least one gate contact connecting to at least one gate conductor.

Noble et al. (US 6,238,976) discloses a vertical Fin-FET semiconductor device characterized by at least one vertical semiconductor fin disposed on an insulator layer Doped source and drain regions in bottom and top portions of the at least one semiconductor fin; and gate conductors disposed along vertical sidewalls of the at least one semiconductor fin and separated therefrom by thin gate insulators; and a vertical channel region in the fin between the source region and the drain region.

Noble et al. does not disclose source conductors contacting the source region on opposite sides of the at least one semiconductor fin; At least one source contact connecting to at least one source conductor; at least one drain contact connecting to the

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drain region of the at least one semiconductor fin; at least one gate contact connecting to at least one gate conductor.

Rudeck (US 6,680,508) discloses a vertical Fin-FET with source and drain regions in the bottom and top portions of the at least one semiconductor fin; with a bit line contacting the drain region.

Rudeck does not disclose source conductors contacting the source region on opposite sides of the at least one semiconductor fin; At least one source contact connecting to at least one source conductor

Huang et al. (IEEE transactions on electron devices) discloses a vertical P-Channel FinFET with gate electrodes formed on both sides of a semiconductor fin.

Huang et al. does not disclose source conductors contacting the source region on opposite sides of the at least one semiconductor fin; At least one source contact connecting to at least one source conductor; at least one drain contact connecting to the drain region of the at least one semiconductor fin; at least one gate contact connecting to at least one gate conductor.

It would not be obvious to modify any of the cited prior art, because none of the prior art discloses a means of connecting a contact to both the source and drain regions of a vertical FinFET, while including a gate contact connected to the gate conductor.

Conclusion

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to KENNETH HAMLIN whose telephone number is (571)270-3341. The examiner can normally be reached on Mon - Fri 9am - 5pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Davienne Monbleau can be reached on 571-272-1945. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/K. H./ Examiner, Art Unit 2893

/Davienne Monbleau/ Supervisory Patent Examiner, Art Unit 2893